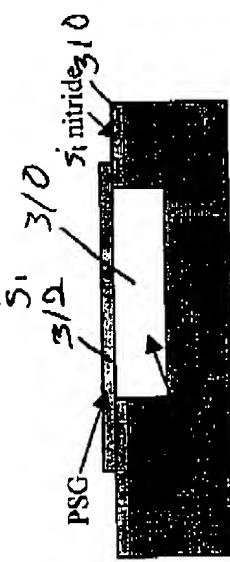
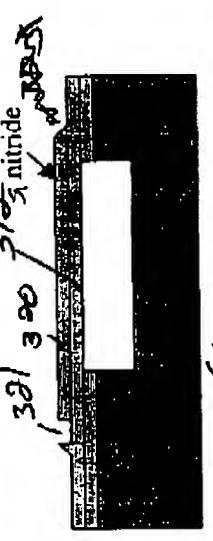


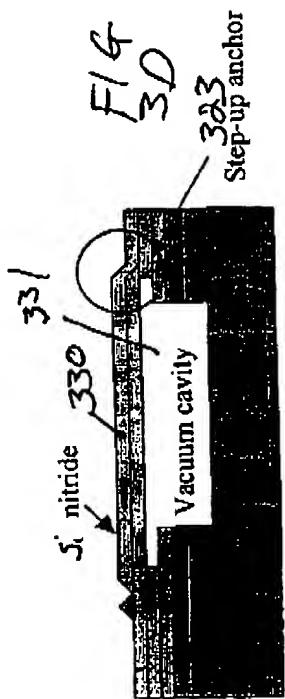
1. Deposit and pattern nitride.



2. Local oxidation. Deposit and pattern phosphosilicate glass(PSG).



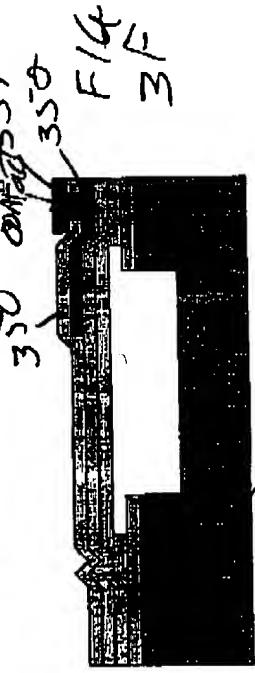
3. Deposit nitride and open etching holes.



4. Remove oxide and PSG by 48%HF.



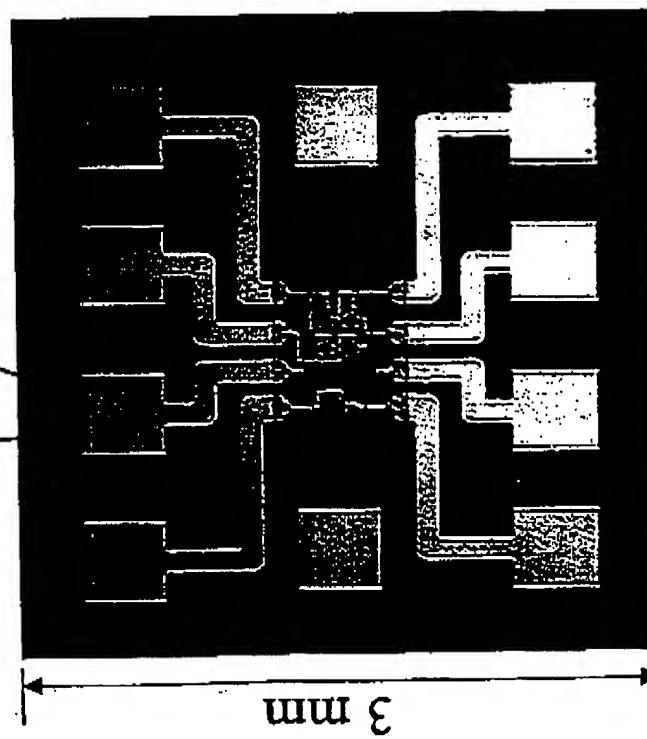
5. Deposit, dope and pattern polysilicon.



6. Deposit nitride as passivation layer and Al metallization.

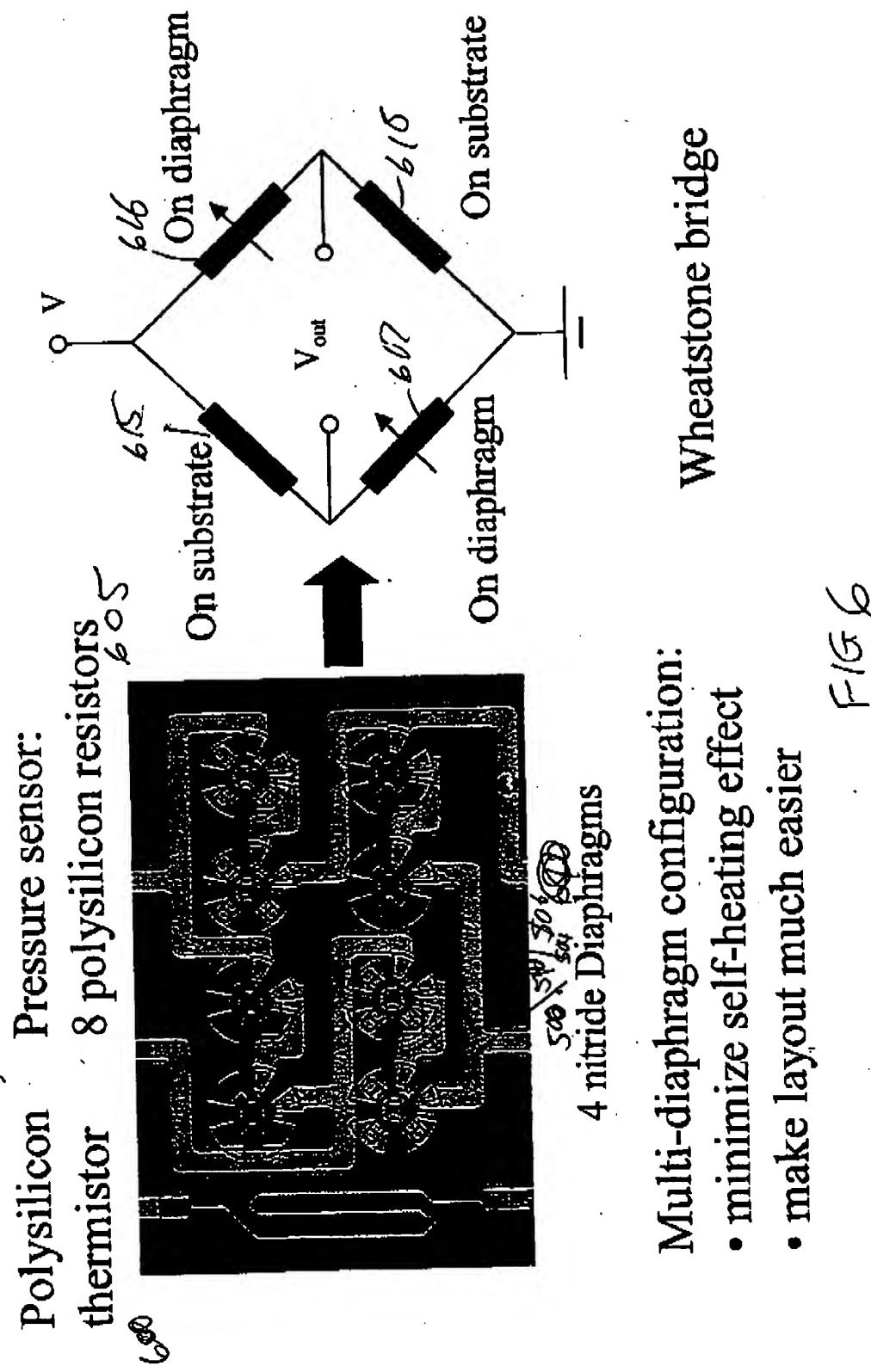
F1G  
3AF1G  
3BF1G  
3C

Fig 4  
400  $\mu$ m Al pads



3 mm

Fig 5  
Chip wire-bonded to metal header



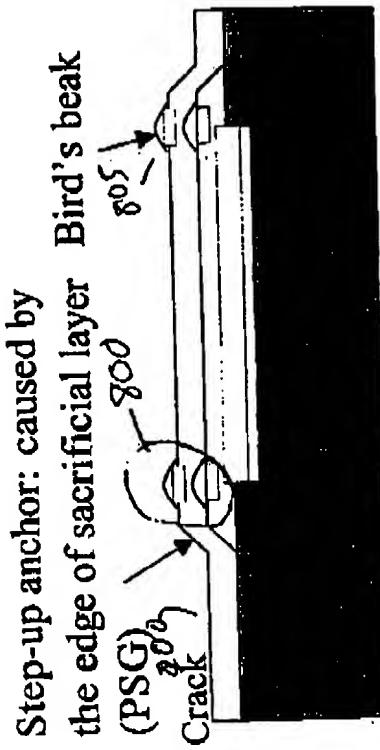


FIG 8  
Cross section of sensor diaphragm

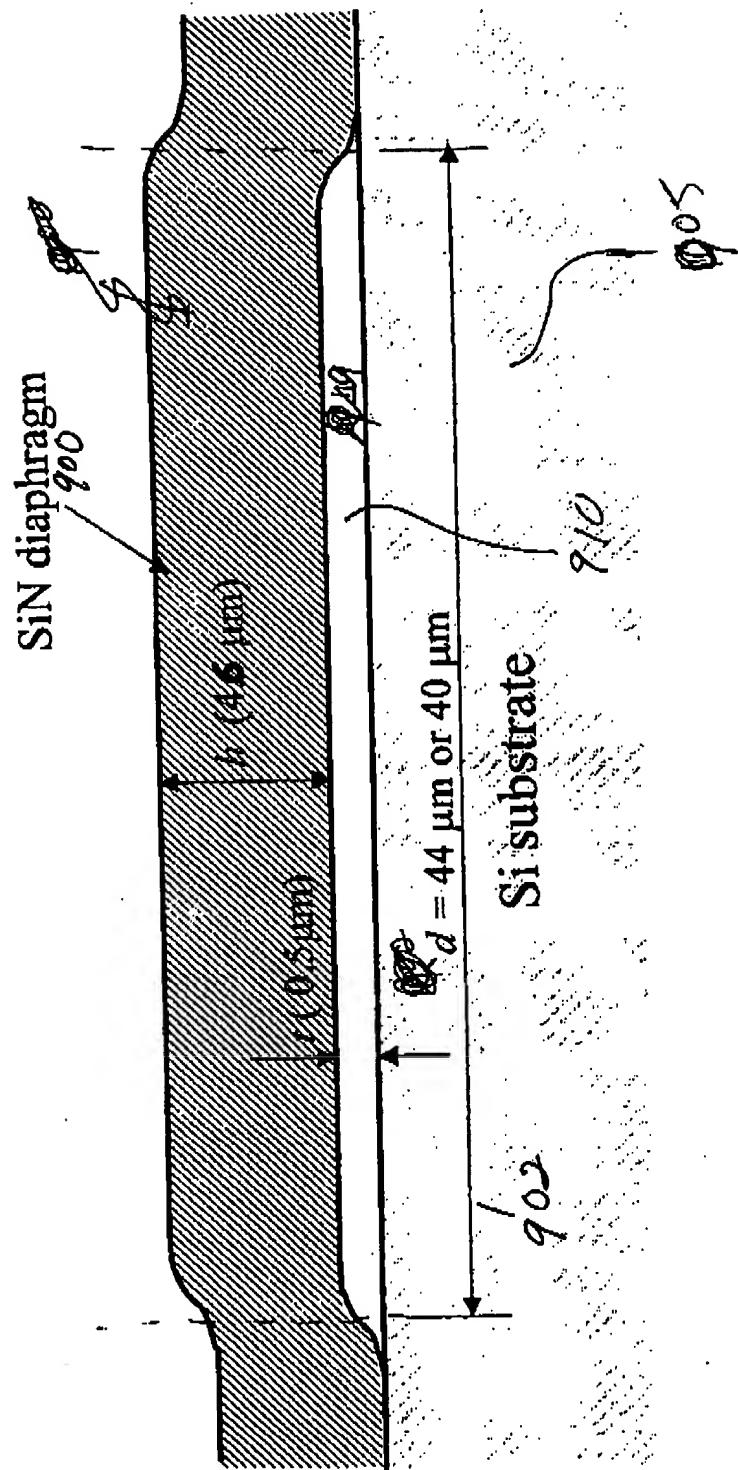


FIG 9

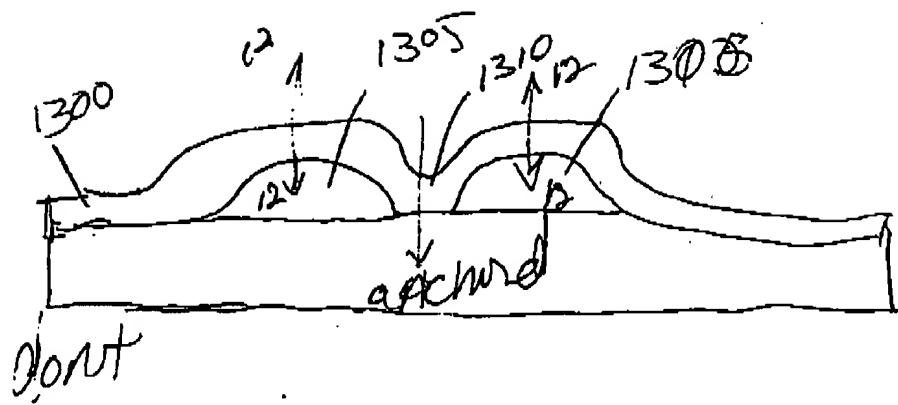
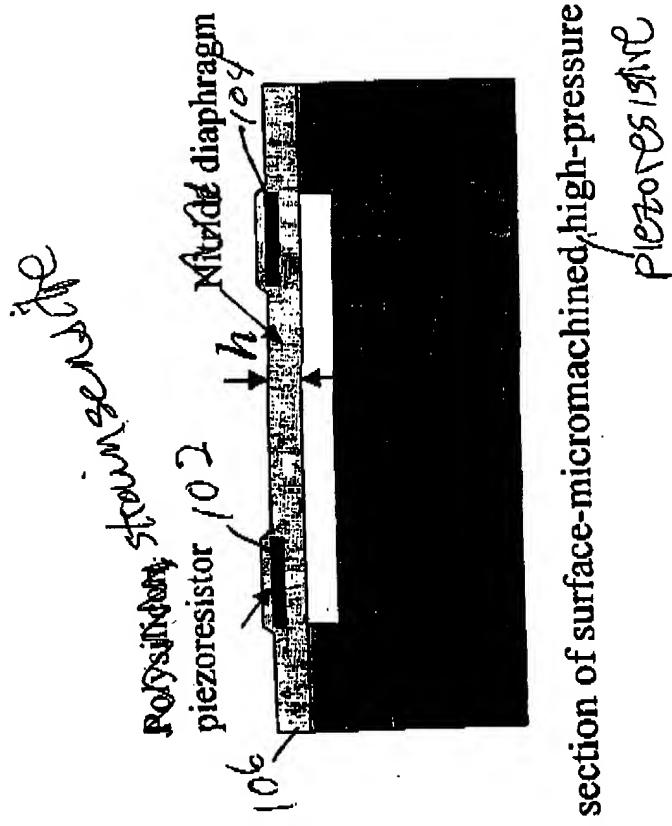


FIG 13



Cross section of surface-micromachined high-pressure sensor  
piezoresistive